
State-of-the-Art Program on Compound Semiconductors 66 (SOTAPOCS 66) & Gallium Nitride and Silicon Carbide Power Technologies

13

Editors:

J. Hite	E. Douglas
M. Dudley	Y. Zhao
Q. Li	B. Raghathamachar
T. Anderson	N. Ohtani
R. Lynch	M. Bakowski
C. O'Dwyer	

Sponsoring Division:



Electronics and Photonics



Published by
The Electrochemical Society
65 South Main Street, Building D
Pennington, NJ 08534-2839, USA
tel 609 737 1902
fax 609 737 2743
www.electrochem.org

ecstransactions™

Vol. 112, No. 2

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Published by:

The Electrochemical Society
65 South Main Street
Pennington, New Jersey 08534-2839, USA

Telephone 609.737.1902
Fax 609.737.2743
e-mail: ecs@electrochem.org
Web: www.electrochem.org

ISSN 1938-6737 (online)

ISBN 978-1-62332-687-6 (PDF)

Printed in the United States of America.

ECS Transactions, Volume 112, Issue 2

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